

0.5µA I_Q, 300mA Linear Regulator

General Description

The EHP8150 features of low quiescent current as low as 0.5μ A and almost zero disable current which is ideal for powering the battery equipment to a longer service life. The EHP8150 guarantees delivery of 300mA output current and can be stable with 1μ F ceramic output capacitor.

The EHP8150 is available in SOT23-3, SOT23-5 and uDFN1X1-4 surface mount packages.

Applications

- Portable, Battery Powered Equipment
- Ultra Low Power Microcontroller
- Notebook computers

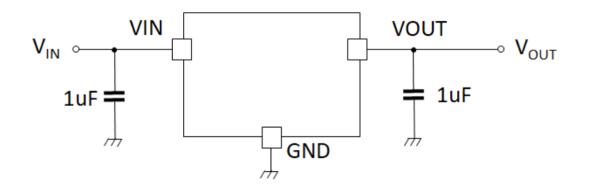
Typical Application

Features

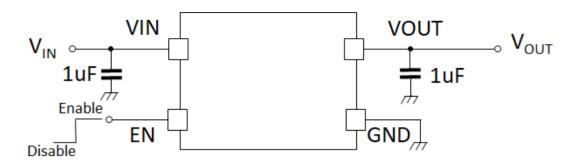
- 2.5V to 5.5V input range
- 300mA output current driving capacity
- 0.5µA typical quiescent current at no Load
- 400mV typical dropout at I_{OUT} = 300mA
- Thermal shutdown protection
- Internal short-circuit current l imit
- Stable with 1µF output capacitor

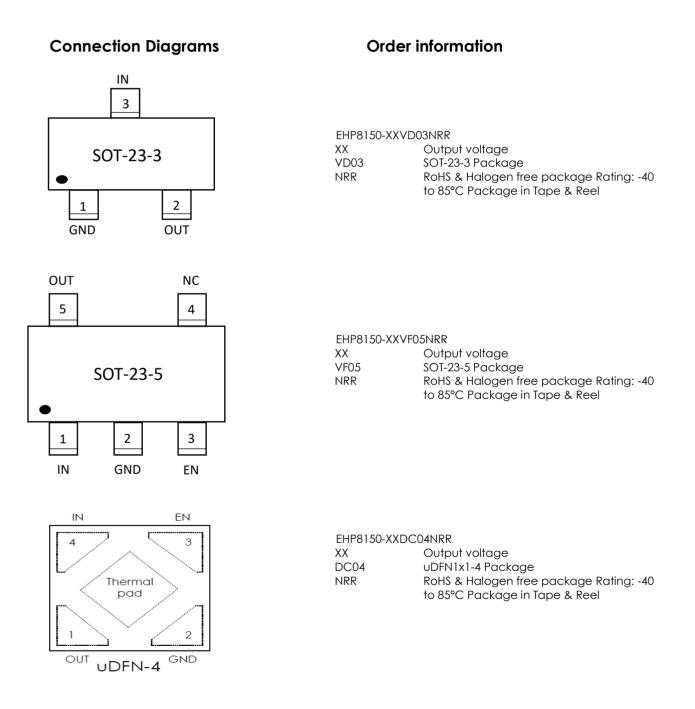
Ordering Information

Part Number	Remark	
EHP8150-XXVD03NRR	±2% output voltage tolerance	
EHP8150-XXVF05NRR	±2% output voltage tolerance	
EHP8150-XXDC04NRR ±2% output voltage tolerance		
XX:12=1.2V, 15=1.5V, 18=1.8V, 25=2.5V, 30=3.0V, 33=3.3V		









Order, Marking and Packing Information

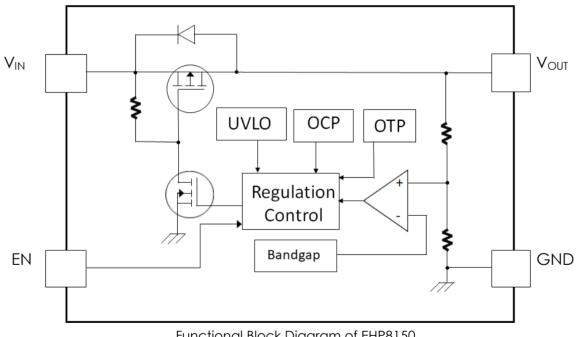
Package	Vout	Product ID.	Marking	Packing
	1.2V	EHP8150-12VD03NRR	3	
	1.5V	EHP8150-15VD03NRR		
SOT-23-3	1.8V	EHP8150-18VD03NRR	SOT-23-3	Tape & Reel 3K pcs
	2.5V	EHP8150-25VD03NRR		
	3.0V	EHP8150-30VD03NRR	1 2	
	3.3V	EHP8150-33VD03NRR		
	1.2V	EHP8150-12VF05NRR	5 4	
	1.5V	EHP8150-15VF05NRR		
SOT-23-5	1.8V	EHP8150-18VF05NRR	SOT-23-5	Tape & Reel 3K pcs
	2.5V	EHP8150-25VF05NRR	•	
	3.0V	EHP8150-30VF05NRR	1 2 3	
	3.3V	EHP8150-33VF05NRR		
DFN1x1-4	1.2V	EHP8150-12DC04NRR	IN EN 4 3 V 1 2 OUT GND	
	1.5V	EHP8150-15DC04NRR	IN EN 4 3 4 3 0 0 0 0 0 0 0 0 0 0 0 0 0	
	1.8V	EHP8150-18DC04NRR	IN EN	Tape & Reel 8K pcs
	2.5V	EHP8150-25DC04NRR	IN EN Code	
	3.0V	EHP8150-30DC04NRR	IN EN 4 X V OUT GND	
	3.3V	EHP8150-33DC04NRR	IN EN 4 X X 0UT GND	



Pin Functions

Name	SOT-23-3	SOT-23-5	uDFN1x1-4	Function
				Supply Voltage Input
V _{IN}	3	1	4	Require a minimum input capacitor of close to 1µF to ensure stability and sufficient decoupling from the ground pin.
GND	1	2	2	Ground Pin
				Enable Input.
EN	N/A	3	3	Enable the regulator by pulling the EN pin High. To keep the regulator on during normal operation, connect the EN pin to VIN. The EN pin must not exceed VIN under all operating conditions.
NC	N/A	4	N/A	No connection
V _{OUT}	2	5	1	Regulated Output Voltage Pin. A small 1µF ceramic capacitor is needed from this pin to ground to assure stability
Thermal Pad	N/A	N/A	YES	The thermal pad with large thermal land area on the PCB will helpful chip power dissipation, to connect it to GND together normally.

Functional Block Diagram



Functional Block Diagram of EHP8150



Absolute Maximum Ratings (Note1, 2)

V _{IN} , EN	-0.3V to 6V	Junction Temperature (TJ)	125°C
Storage Temperature Range	-65°C to 150°C	Lead Temperature (Soldering, 10 sec.)	260°C
		ESD Rating	
		Human Body Model	2KV

Recommended Operating Conditions (Note1, 2)

Supply Voltage	2.5V to 5.5V	Operating Temperature Range	-40°C to 85°C

Thermal Resistance:

Symbol	θ _{JA} (Note3)	θ Jc(Note4)
SOT23-3	250(°C/W)	81(°C/W)
SOT23-5	152(°C/W)	81(°C/W)
uDFN1x1-4	110(°C/W)	23(°C/W)

Electrical Characteristics

Unless otherwise specified, all limits guaranteed for $V_{IN}=V_{EN}=V_{OUT}+1V$, $C_{IN}=C_{OUT}=1$ uF, $T_{a}=25^{\circ}$ C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Output Voltage Accuracy			-2%		2%	V
Line Regulation		$V_{IN}=V_{OUT}$ + 1V to 5.5V,		20	50	mV
		Iout= 1mA to 150mA		12	30	
Load Regulation	$\triangle V_{LOAD}$	lout= 1mA to 300mA		25	60	mV
		I _{оит} =100mA		130		mV
Dropout Voltage	Vdrop	I _{олт} =300mA		400		mV
Quiescent Current	lq	T」= 25°C		0.5	1	υA
Current Limit	Icl		360	560		mA
Enable high level	VENHI		0.6			V
Enable low level	V _{ENLO}				0.2	V
Thermal Shutdown	TSD			150		°C
Thermal ShutdownHysteresis	Тнү			20		°C
Power-supply rejection ratio	PSRR	f = 1kHz		60		dB

Note 1: Absolute Maximum ratings indicate limits beyond which damage may occur. Electrical specifications do not apply when operating the device outside of its rated operating conditions.

Note 2: All voltages are with respect to the potential at the ground pin.

Note 3: θ_{JA} is measured in the natural convection at TJ=25°C on a high effective thermal conductivity test board (2 layers, 2S0P).

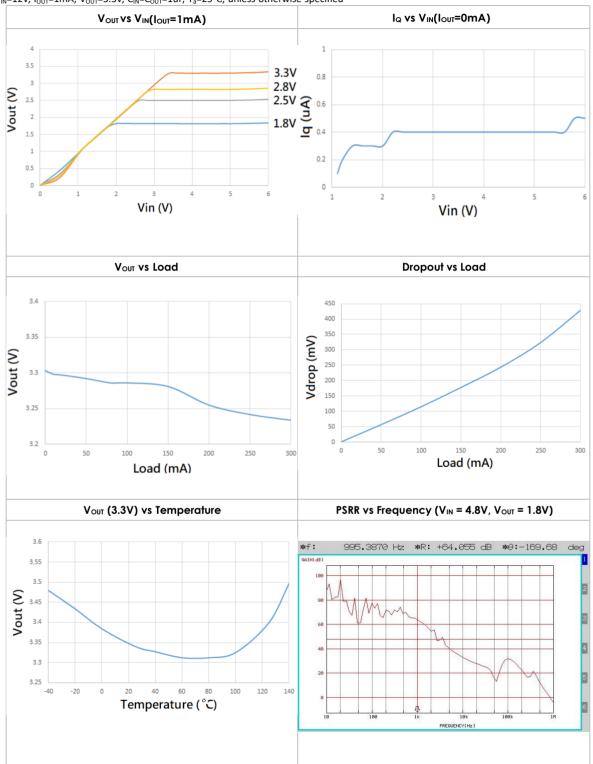
Note 4: θ_{JC} represents the resistance to the heat flows the chip to package top case.

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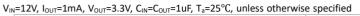


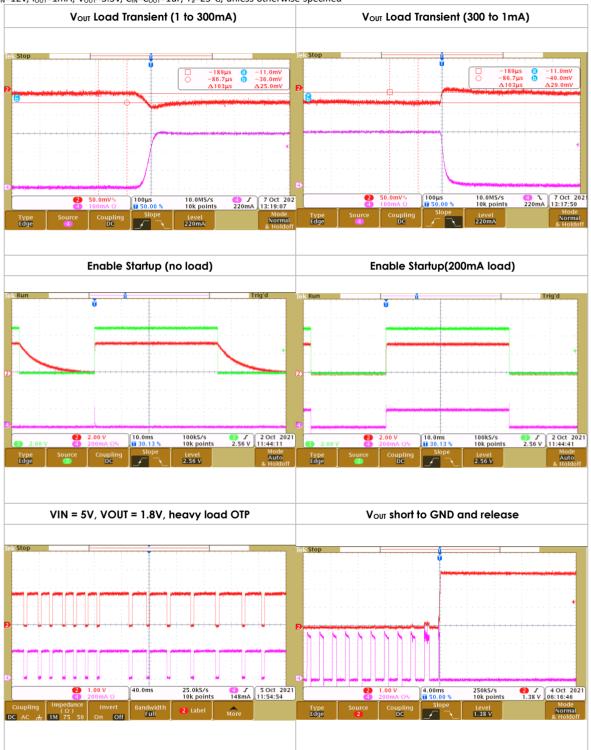
Typical Performance Characteristics

 $V_{IN}{=}12V,\ I_{OUT}{=}1mA,\ V_{OUT}{=}3.3V,\ C_{IN}{=}C_{OUT}{=}1uF,\ T_a{=}25^\circ C,\ unless\ otherwise\ specified$



Typical Performance Characteristics (cont.)





Application Information

Output Capacitor

The EHP8150 is specially designed for use with ceramic output capacitors of as low as 1 μ F to take advantage of the savings in cost and space as well as the superior filtering of high frequency noise. Capacitors of higher value or other types may be used, but it is important to make sure its equivalent series resistance (ESR) is restricted to than 0.5 Ω . The use of larger capacitors with smaller ESR values is desirable for applications involving large and fast input or output transients, as well as for situations where the application systems are not physically located immediately adjacent to the battery power source. Typical ceramic capacitors suitable for use with the EHP8150 are X5R and X7R. The X5R and the X7R capacitors are able to maintain their capacitance values to within ±20% and ±10%, respectively, as the temperature increases.

Input Capacitor

A minimum input capacitance of 1µF is required for EHP8150. The capacitor value may be increased without limit. Improper workbench set-ups may have adverse effects on the normal operation of the regulator. A case in point is the instability that may result from long supply lead inductance coupling to the output through the gate capacitance of the pass transistor. This will establish a pseudo LCR network, and is likely to happen under high current conditions or near dropout. A 10µF tantalum input capacitor will dampen the parasitic LCR action thanks to its high ESR. However, cautions should be exercised to avoid regulator short-circuit damage when tantalum capacitors are used, for they are prone to fail in short-circuit operating conditions.

Power Dissipation and Thermal Shutdown

Thermal overload results from excessive power dissipation that causes the IC junction temperature to increase beyond a safe operating level. The EHP8150 relies on dedicated thermal shutdown circuitry to limit its total power dissipation. An IC junction temperature T_J exceeding 150°C will trigger the thermal shutdown logic, turning off the P-channel MOS pass transistor. The pass transistor turns on again after the junction cools off by about 20°C. When continuous thermal overload conditions persist, this thermal shutdown action then results in a pulsed waveform at the output of the regulator. The concept of thermal resistance θ_{JA} (°C/W) is often used to describe an IC junction's relative readiness in allowing its thermal energy to dissipate to its ambient air. An IC junction with a low thermal resistance is preferred because it is relatively effective in dissipating its thermal energy to its ambient, thus resulting in a relatively low and desirable junction temperature. The relationship between θ_{JA} and T_J is as follows:

$T_{J} = \Theta_{JA} \times (P_{D}) + T_{A}$

 T_{A} is the ambient temperature, and P_{D} is the power generated by the IC and can be written as:

PD = IOUT (VIN - VOUT)

As the above equations show, it is desirable to work with ICs whose θ_{JA} values are small such that T_J does not

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ESMT

EHP8150

increase strongly with P_D. To avoid thermally overloading the EHP8150, refrain from exceeding the absolute maximum junction temperature rating of 125°C under continuous operating conditions. Overstressing the regulator with high loading currents and elevated input-to-output differential voltages can increase the IC die temperature significantly.

Maximum power dissipation for the device is calculated using the following equation:

$$PD = \frac{TJ(max) - TA}{\Theta JA}$$

Where TJ(MAX) is the maximum junction temperature, T_A is the ambient temperature, and θ J_A is the junction-to-ambient thermal resistance. For example,

for the SOT-23-3 package θ_{JA} =250°C/W, TJ(MAX)=125°C and using TA=25°C, the maximum power dissipation is 0.4W. for the SOT-23-5 package θ_{JA} =152°C/W, TJ(MAX)=125°C and using TA=25°C, the maximum power dissipation is 0.65W. for the SOT-89-3 package θ_{JA} =90°C/W, TJ(MAX)=125°C and using T_A=25°C, the maximum power dissipation is 1.1W.

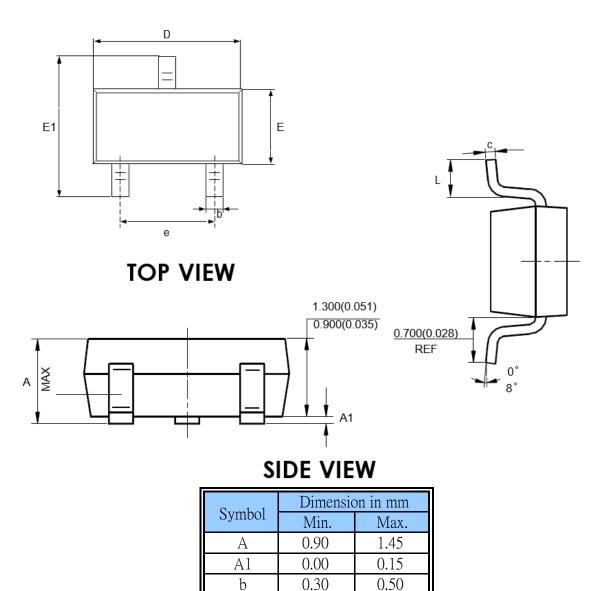
Shutdown

The EHP8150 enters the sleep mode when the EN pin is low. When this occurs, the pass transistor, the error amplifier, and the biasing circuits, including the bandgap reference, are turned off, thus reducing the supply current to typically 0.5µA. Such a low supply current makes the EHP8150 best suited for battery-powered applications. The maximum guaranteed voltage at the EN pin for the sleep mode to take effect is 0.2V.



EHP8150

Package Outline Drawing SOT-23-3



0.10

2.82

1.50

2.65

1.80

0.30

c D

Е

E1

е

L

0.20

3.10

1.70

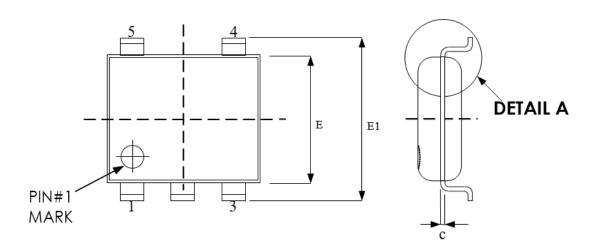
3.00

2.00

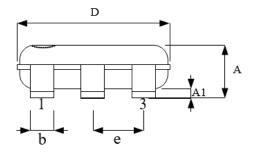
0.60

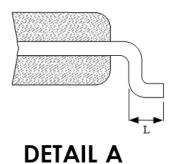


Package Outline Drawing SOT-23-5



TOP VIEW





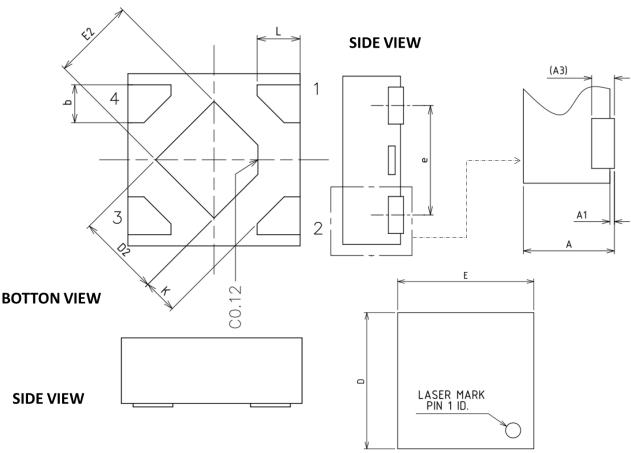
SIDE VIEW

Coursels a 1	Dimension in mm		
Symbol	Min.	Max.	
А	0.90	1.45	
A1	0.00	0.15	
b	0.30	0.50	
С	0.08	0.25	
D	2.70	3.10	
Е	1.40	1.80	
E1	2.60	3.00	
e	0.95 BSC		
L	0.30	0.60	

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Package Outline Drawing uDFN-4L (1mm x 1mm)



TOP VIEW

0 1 1	Dimension in mm			
Symbol	Min.	Тур.	Max.	
А	0.34	0.37	0.40	
A1	0.00	0.02	0.05	
A3		0.10	0.50	
b	0.17	0.22	0.27	
D	0.95	1.00	1.05	
D2	0.43	0.48	0.53	
Е	0.95	1.00	1.05	
E2	0.43	0.48	0.53	
е		0.65		
L	0.20	0.25	0.30	
K	0.15			

Revision History

Revision	Date	Description
0	2022.3.16	Original
1	2022.3.17	Add Notes/Thermal Resistance and make corrections.
1.1	2022.6.10	Modify some errors

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